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cont'd

annealing temperature. When the annealing process is conducted at 350°, the H₂ gas is supplied with a flow-rate of 400 SCCM. It should be noted that the order of the foregoing steps S6 and S7 may be exchanged.

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Next, in the step of FIG.16 corresponding to the step S16 of FIG.10, the structure of FIG.15 is subjected to an annealing process conducted in a gas atmosphere. In the step of FIG.16, an H₂ gas or an N₂ gas is used for the annealing atmosphere and the annealing is conducted under a reduced pressure of at least 10 Pa, preferably 670 Pa, at a temperature of 300-350°C over a duration of about 5 minutes while supplying the reducing gas with a flow-rate of 400 SCCM. It should be noted that the duration of the annealing process depends on the annealing temperature.

See the attached Appendix for the changes made to effect the above paragraph

IN THE CLAIMS:

Please amend claims 1, 4, 5 and 11 to read as follows:

1. (Amended) A method for fabrication a semiconductor device, comprising the steps of:

forming a barrier conductor layer on a substrate;

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exposing said barrier conductor layer to a first gas atmosphere containing a reducing gas at an elevated substrate temperature;

forming, after said step of exposing said barrier conductor layer to said first gas atmosphere, a metal film on said barrier conductor layer by a CVD process; and